ABSTRACT

A method for manufacturing a semiconductor device comprising a nonvolatile memory transistor of a stacked gate structure having a floating gate and a control gate, and a MOS transistor of a single gate structure, wherein the method comprises the steps of forming a first insulation film that becomes a gate oxide film of the transistors on a semiconductor substrate; forming a first conductive layer on the first insulation film; removing, from the first conductive layer, a region for separating a floating gate in a direction perpendicular to a direction in which the control gate is formed extendedly; forming a second insulation layer on the first conductive layer; forming a second conductive layer on the second insulation film; patterning the second conductive layer so as to form the control gate; and patterning the first conductive layer to form the stacked gate structure and the single gate structure.

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